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## **Photonic Devices Based on Porous Silicon Layers**

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### **Abstract**

The optoelectronic properties of (Al/c-Si) and sandwich structure type (Al/PS/c-Si/Al) were reported. The nanostructure porous silicon is obtained by photochemical etching without applying electric field.

The photosensitivity of (Al/PS/c-Si/Al) structure is determined by porous layer photoconduction. Maximum spectral sensitivity of the

Porous layer is changed from (575-610)nm depending on preparation condition.